

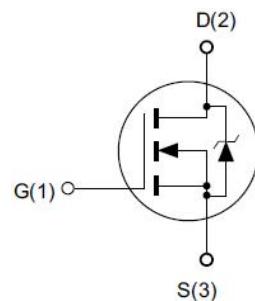


# MPF20N60

## N-Channel Power MOSFET

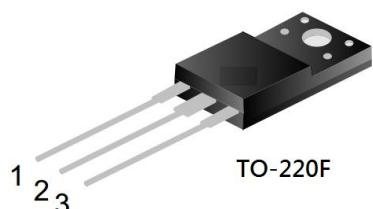
### Features

- ◆ 600V, 20A,  $R_{DS(ON)}$ (Typ.) = 0.35Ω@VGS = 10V.
- ◆ Low Crss
- ◆ Fast Switching
- ◆ 100% Avalanche Tested



### Application

- ◆ Adaptor
- ◆ Standby Power
- ◆ Switching power supply



### Absolute Maximum Ratings $T_c = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Limit	Unit
		TO-220F	
$V_{DS}$	Drain-Source Voltage <sup>a</sup>	600	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-Continuous, $T_c = 25^\circ\text{C}$	20	A
	Drain Current-Continuous, $T_c = 100^\circ\text{C}$	12.5	A
$I_{DM}$	Drain Current-Pulsed <sup>b</sup>	80	A
$P_D$	Maximum Power Dissipation @ $T_J = 25^\circ\text{C}$	86	W
EAS	Single Pulsed Avalanche Energy <sup>c</sup>	980	mJ
$T_J, T_{STG}$	Operating and Store Temperature Range	-55 to 150	°C

### Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	1.45	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max.	62.5	°C/W

### Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

#### Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	600	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$	-	-	1	μA
$I_{GSS}$	Forward Gate Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 30\text{V}$	-	-	$\pm 100$	nA



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### ■ On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance <sup>c</sup>	$V_{GS} = 10V$ , $I_D = 10A$	-	0.35	0.45	$\Omega$

### ■ Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$C_{iss}$	Input Capacitance	$V_{DS} = 25V$ , $V_{GS} = 0V$ , $f = 1.0MHz$	-	2800	-	pF
$C_{oss}$	Output Capacitance		-	260	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	25	-	pF

### ■ On Characteristics

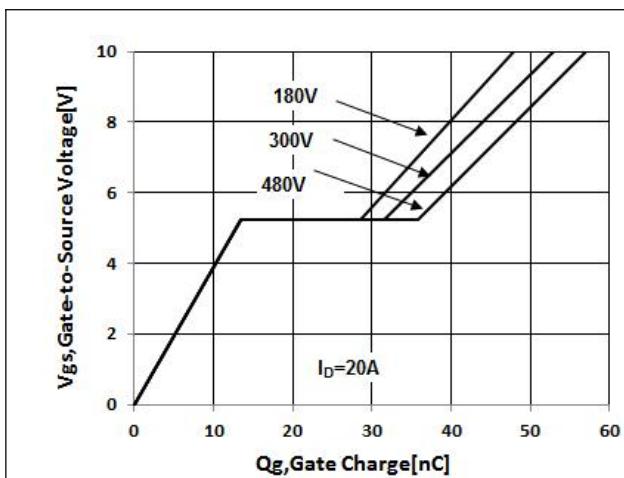
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300V$ , $I_D = 20A$ , $V_{GS} = 10V$	-	36	-	ns
$t_r$	Turn-On Rise Time		-	73	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	166	-	ns
$t_f$	Turn-Off Fall Time		-	73	-	ns
$Q_g$	Total Gate Charge	$V_{DS} = 300V$ , $I_D = 20A$ , $V_{GS} = 10V$	-	53.5	-	nC
$Q_{gs}$	Gate-Source Charge		-	13.5	-	nC
$Q_{gd}$	Gate-Drain Charge		-	19.3	-	nC

### ■ Drain-Source Diode Characteristics

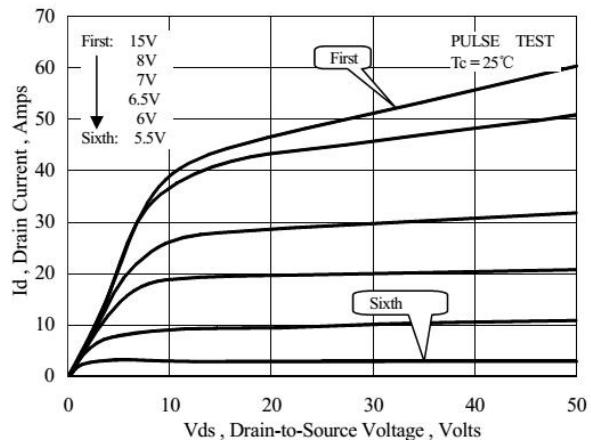
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$I_s$	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	20	A
$I_{SM}$	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	80	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0V$ , $I_s = 20A$	-		1.4	V
$T_{rr}$	Body Diode Reverse Recovery Time	$di/dt = 100A/\mu s$ $I_s = 20A$ , $V_{GS} = 0V$	-	530	-	ns
$Q_{rr}$	Reverse Recovery Charge		-	6.1	-	uC

Notes:

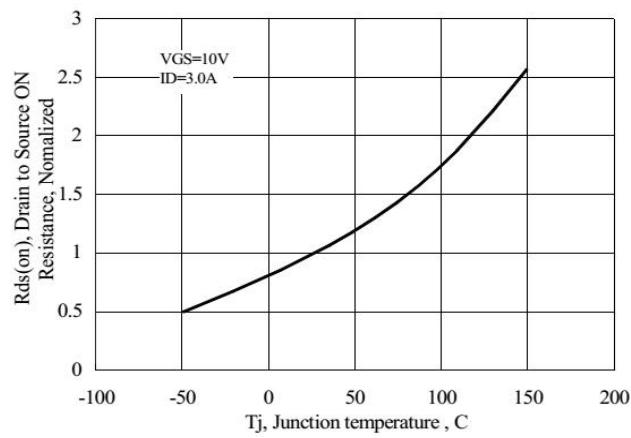
- a.  $T_J = +25^\circ C$  to  $+150^\circ C$
- b. Repetitive rating; pulse width limited by maximum junction temperature.
- c. Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$
- d.  $L = 10mH$ ,  $I_{AS} = 14A$ ,  $V_{DD} = 50V$ ,  $R_G = 25\Omega$  Starting  $T_J = 25^\circ C$ .



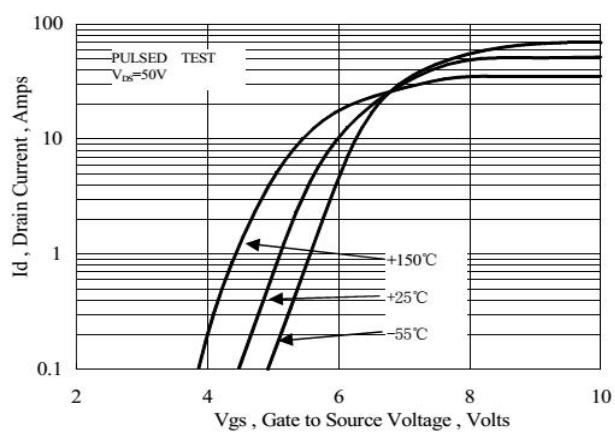
**Figure 1. Gate Charge Characteristics**



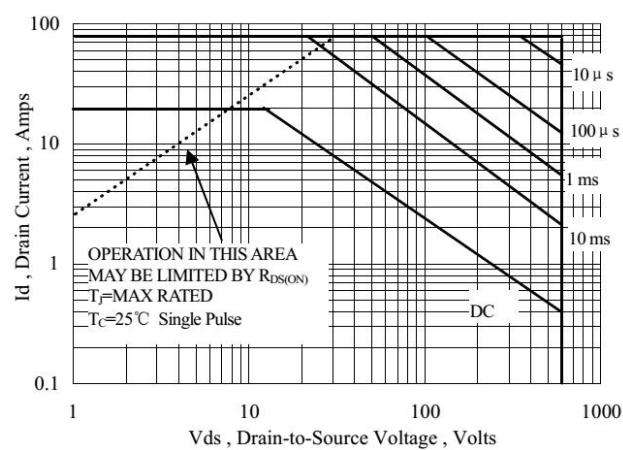
**Figure 2. On-State Characteristics**



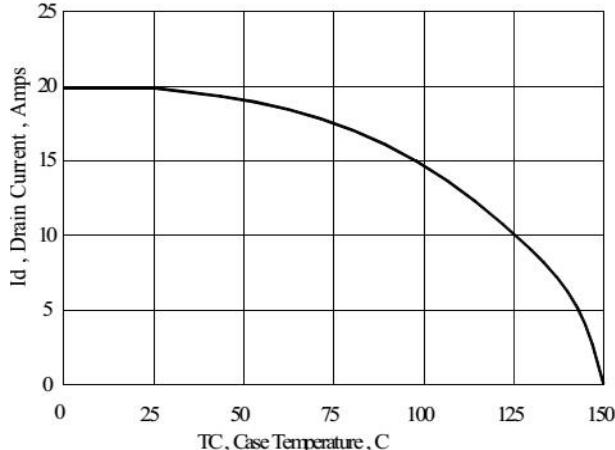
**Figure 3. Normalized On-Resistance Variation with Temperature**



**Figure 4. Transfer Characteristics**



**Figure 5. Maximum Forward Bias Safe Operating Area TO-220F**



**Figure 6. Maximum Continuous Drain Current vs Case Temperature**

## ■ Package Information

